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(54) **ACTIVE MATRIX ORGANIC LIGHT
EMITTING DISPLAY AND METHOD OF
FORMING THE SAME**

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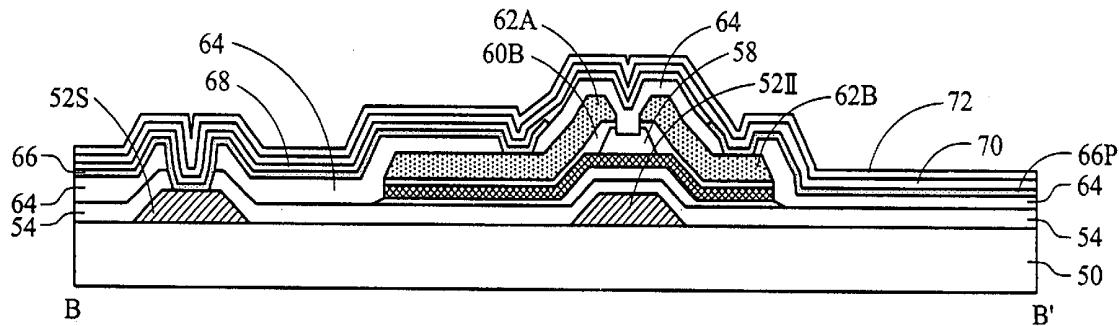
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(57) **ABSTRACT**

An active matrix organic light emitting display (AM-OLED) and a method of forming the same. The AM-OLED has a plurality of pixel areas arranged in a matrix form. Each pixel area has at least two amorphous silicon TFTs, a display area and a light-shielding layer. The amorphous silicon TFT has an amorphous silicon layer serving as a channel region. The display area is formed by a transparent-conductive layer. The light-shielding layer covers at least the amorphous silicon layer of the amorphous silicon TFT and exposes the display area.



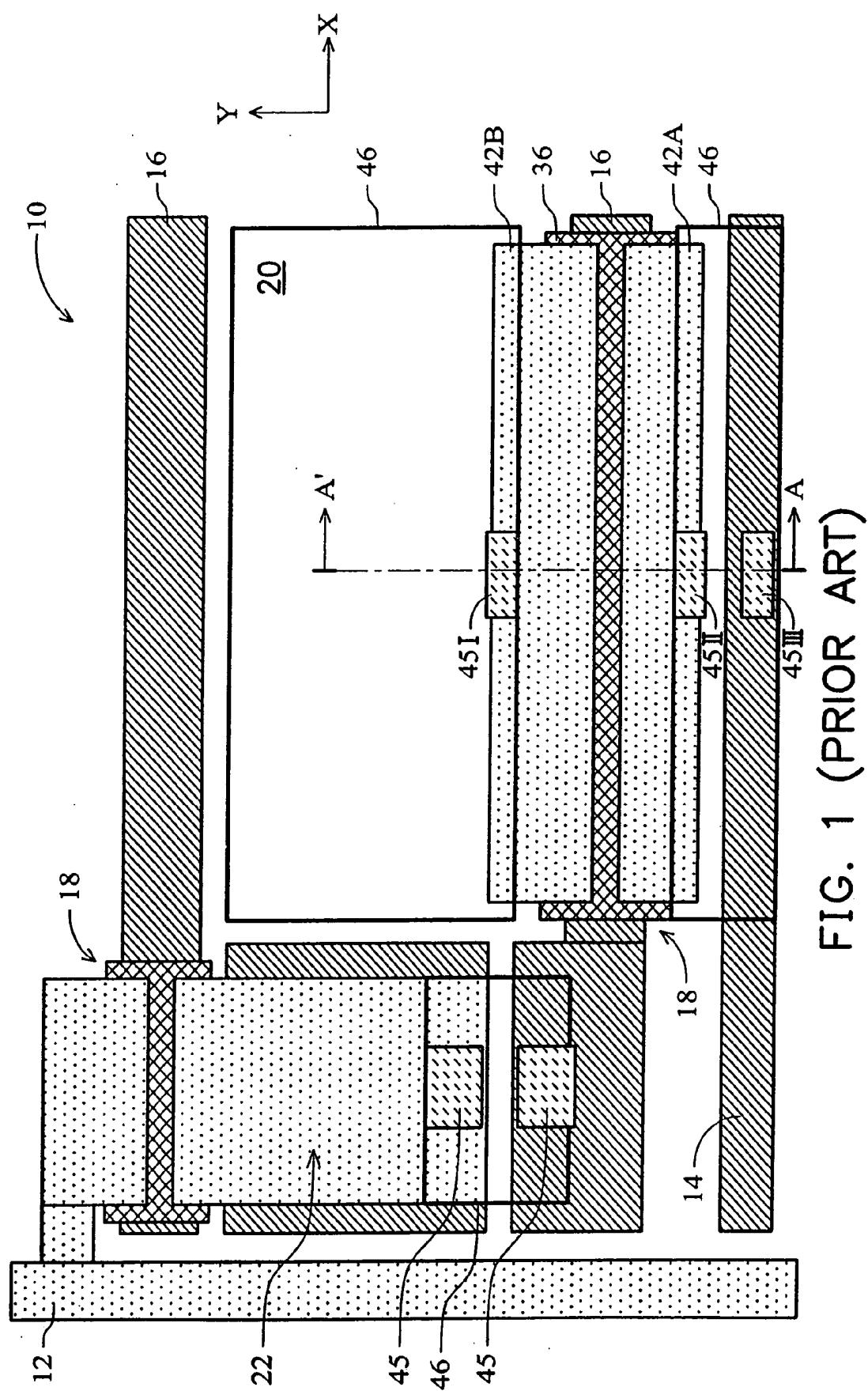


FIG. 1 (PRIOR ART)

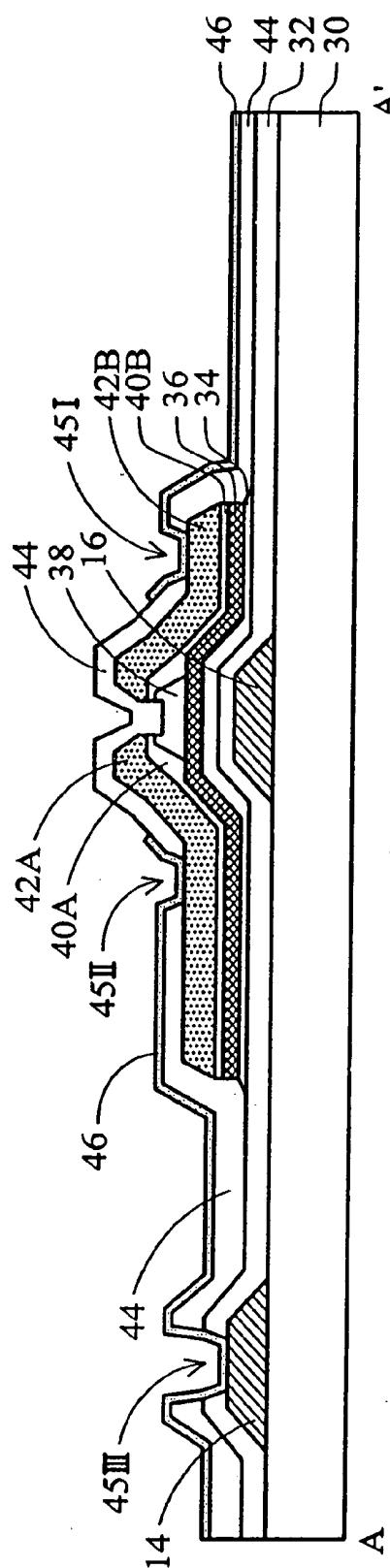


FIG. 2A (PRIOR ART)

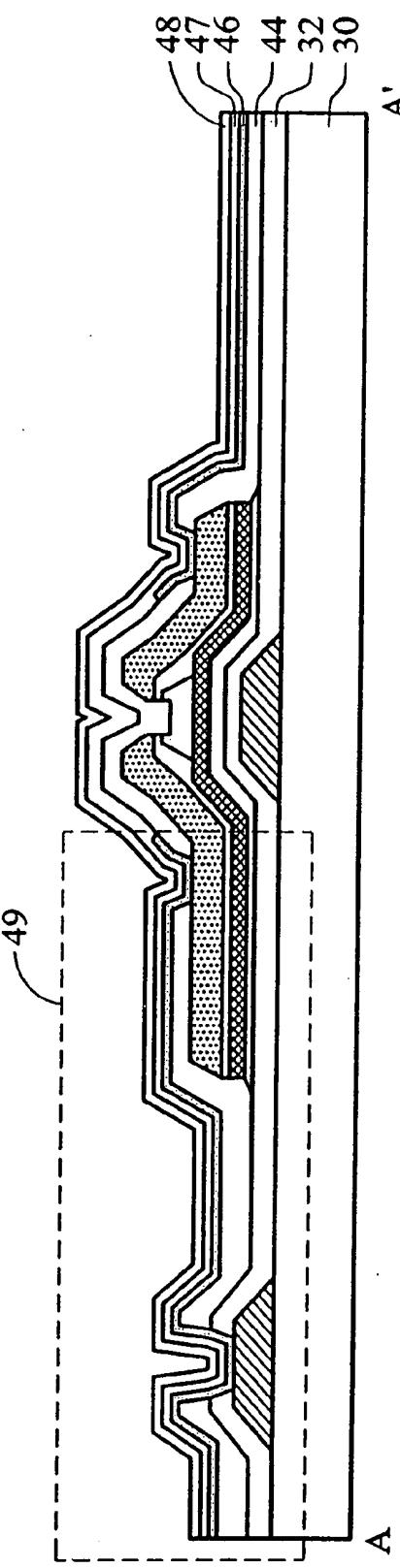


FIG. 2B (PRIOR ART)

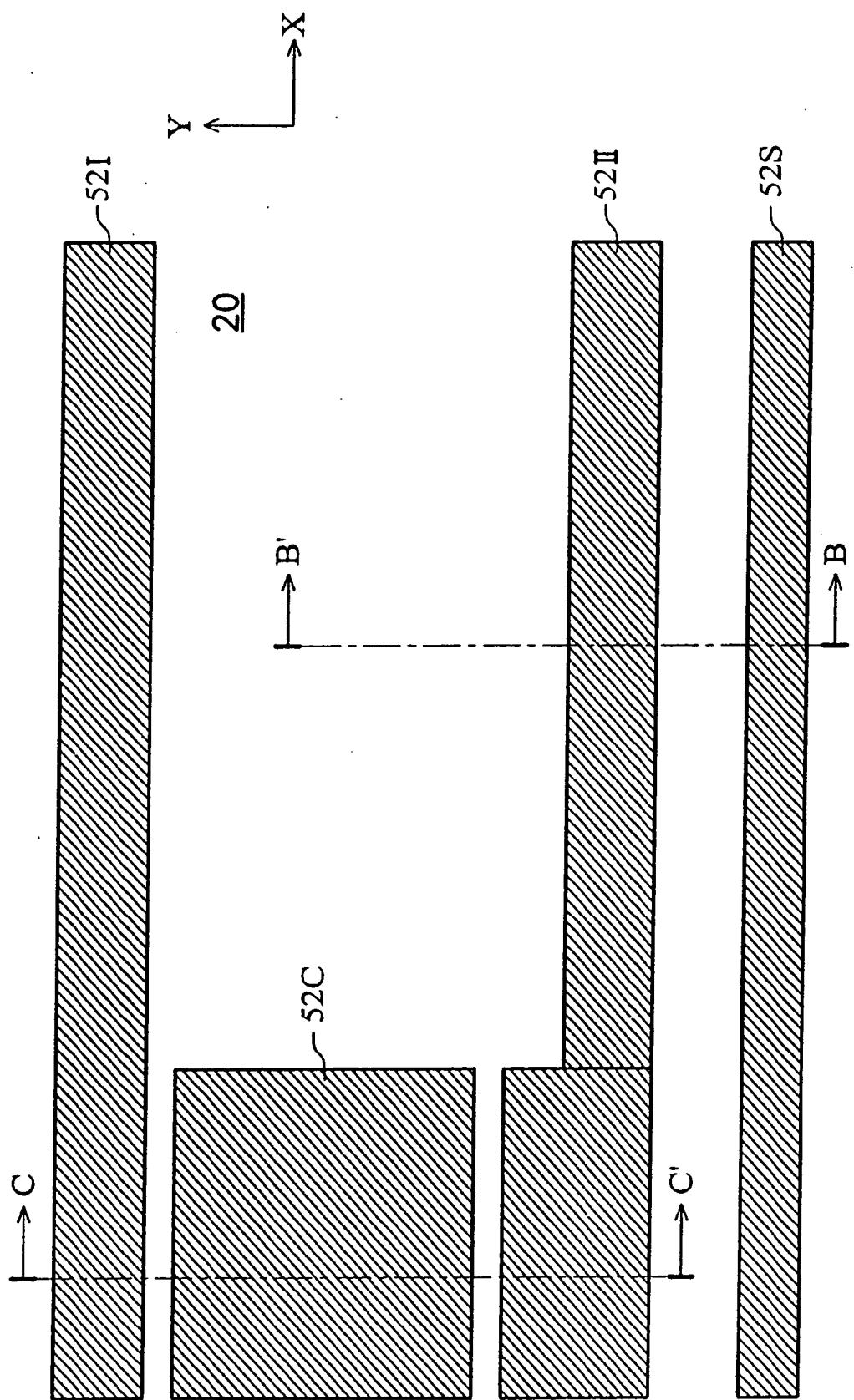


FIG. 3A

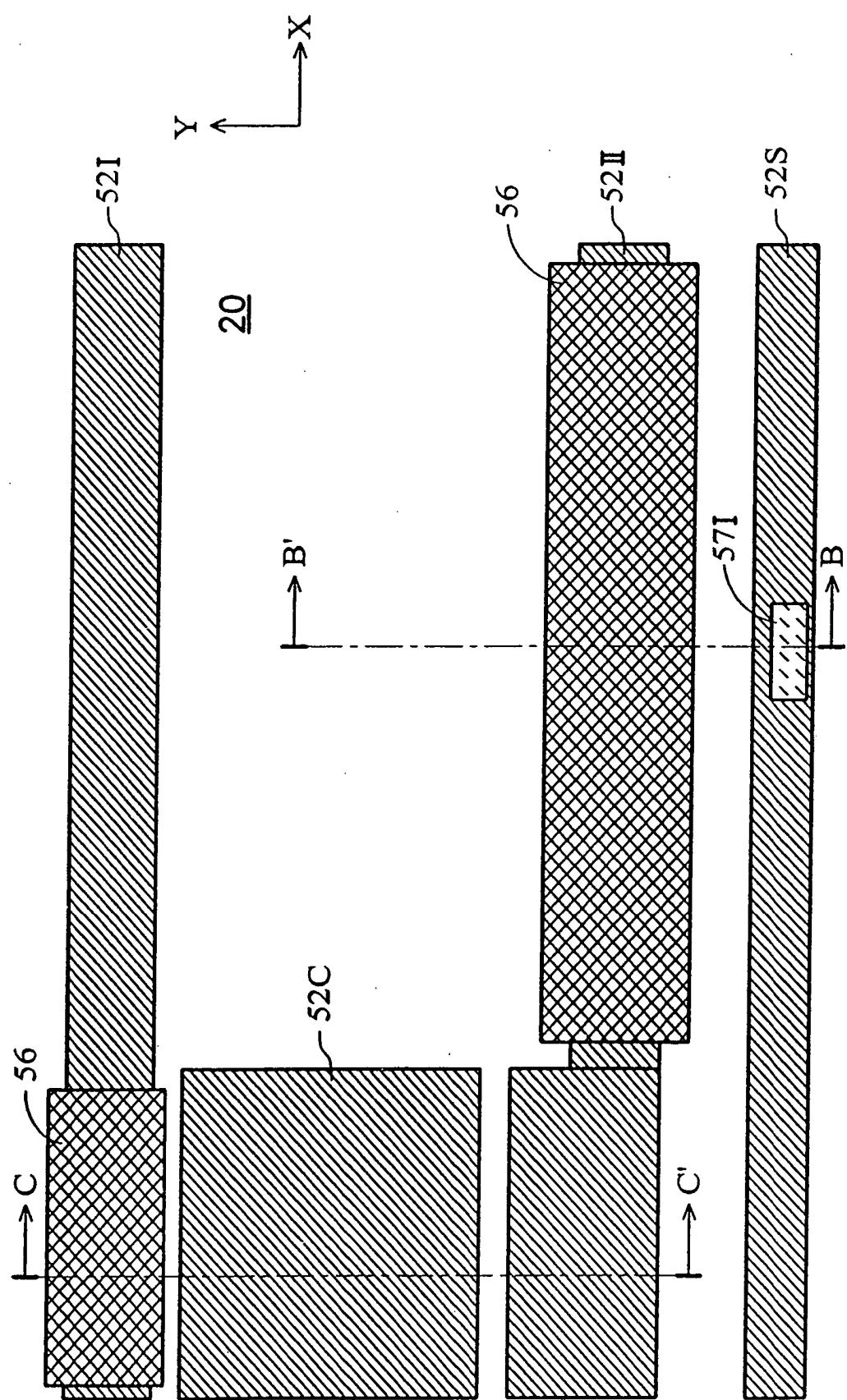


FIG. 3B

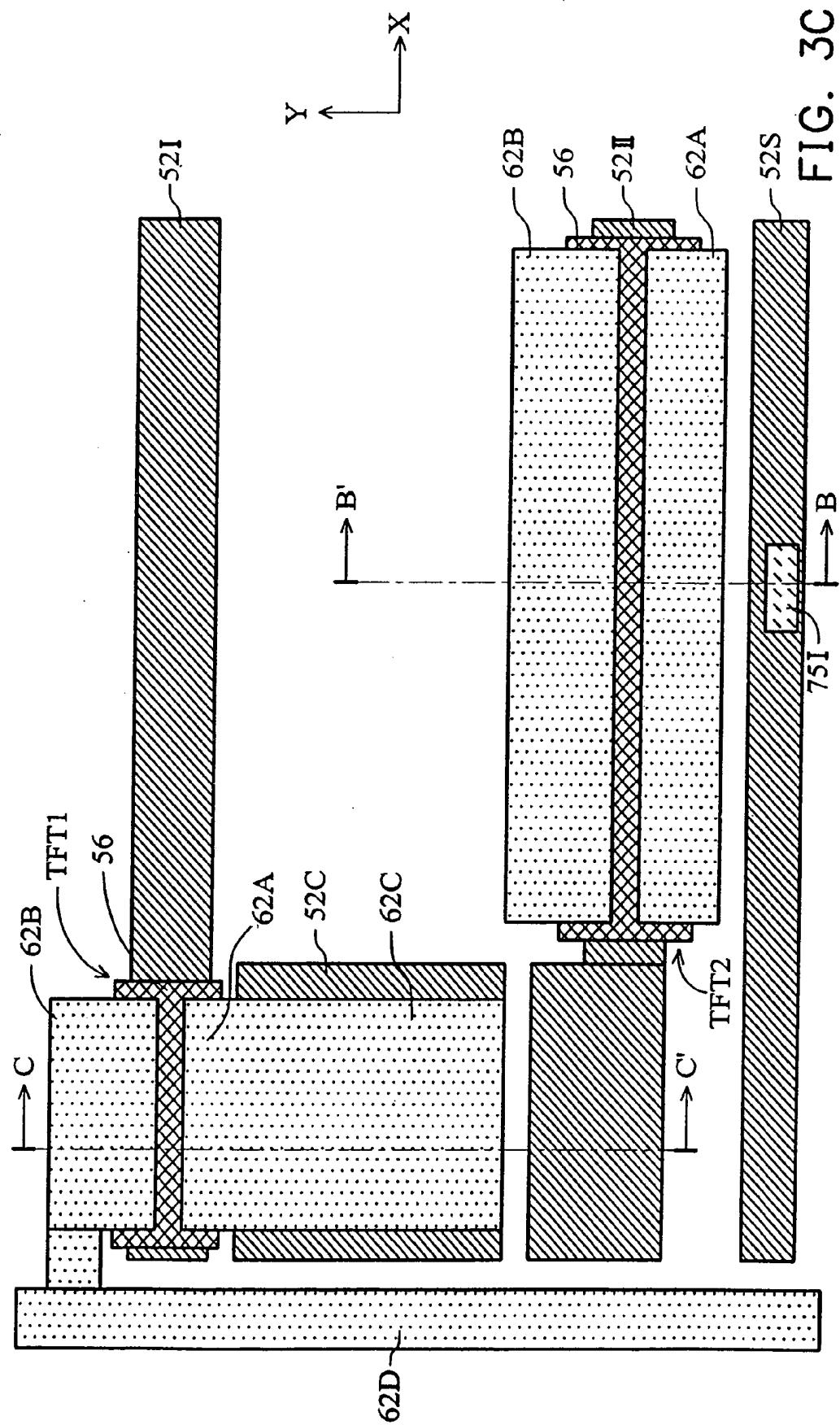
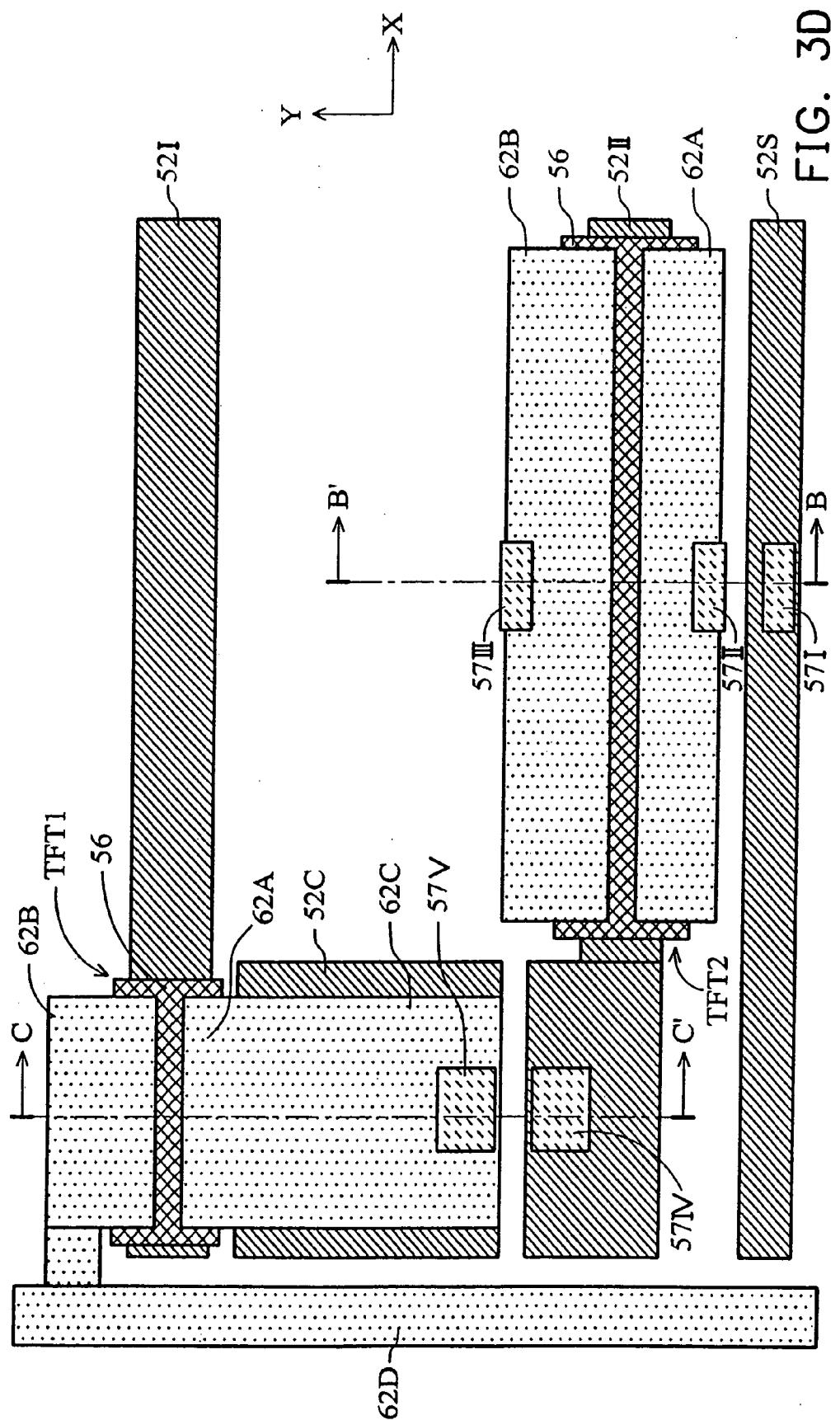


FIG. 3C



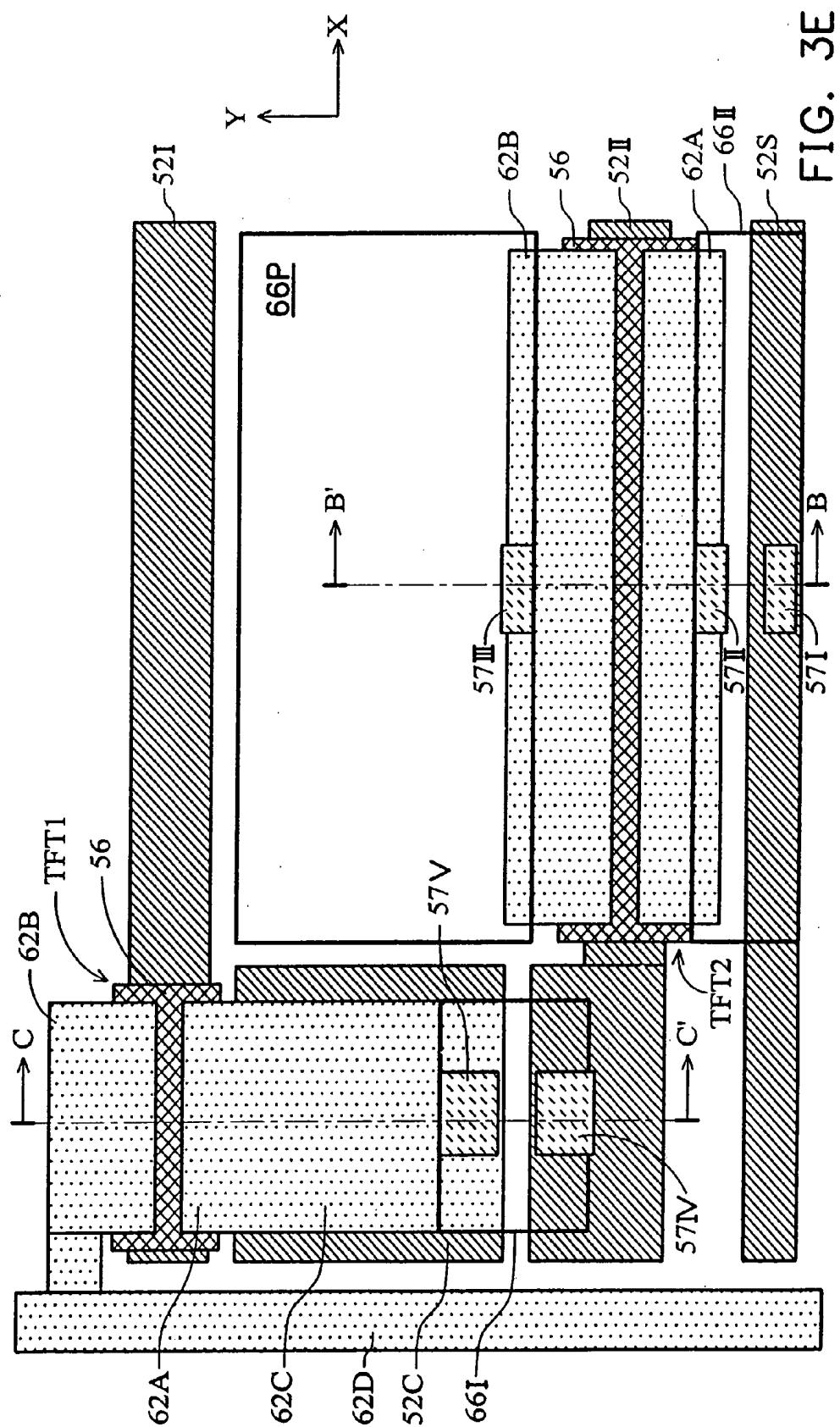
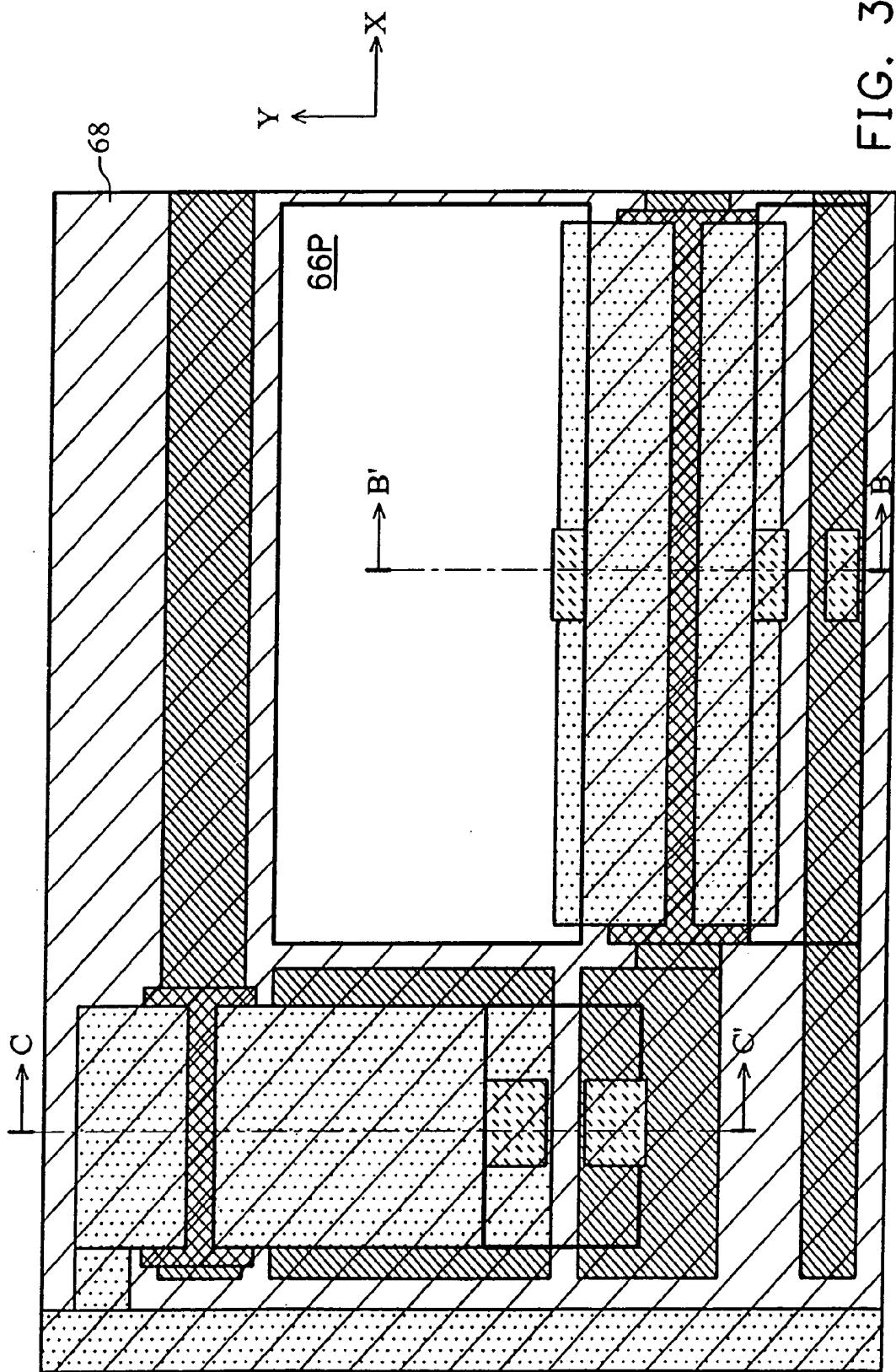
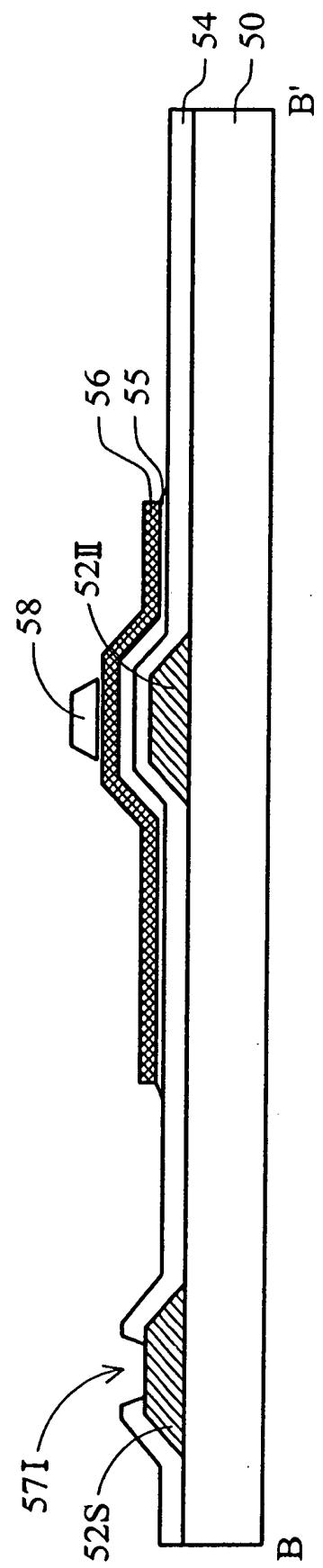
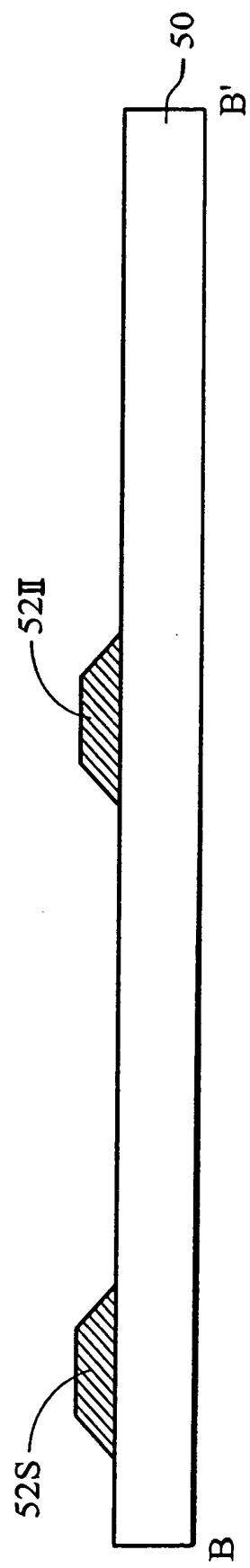


FIG. 3F





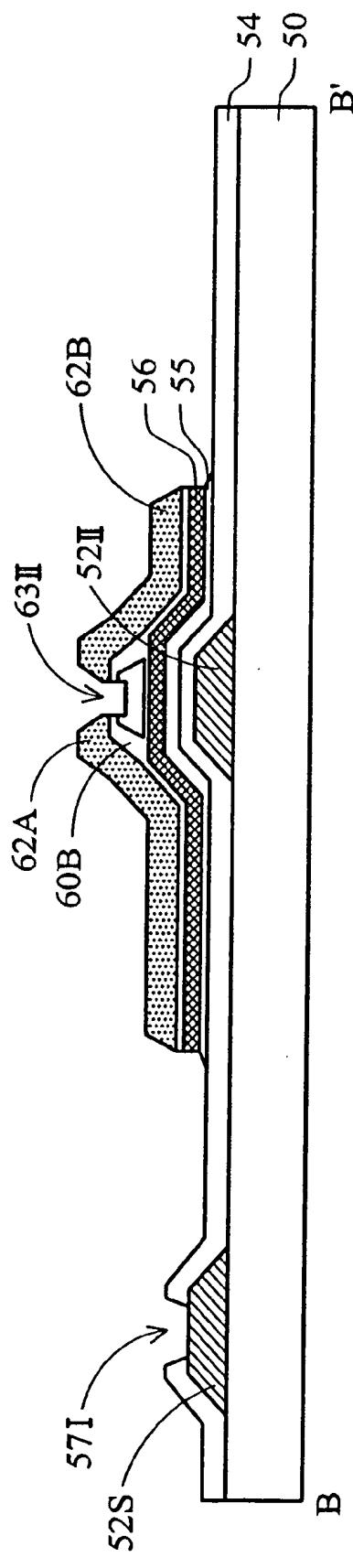


FIG. 4C

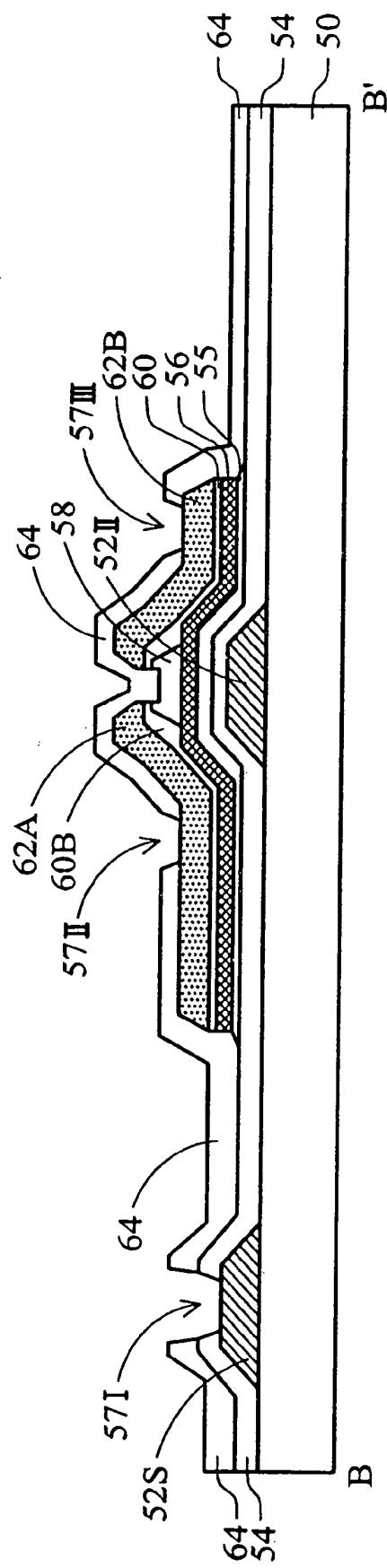


FIG. 4D

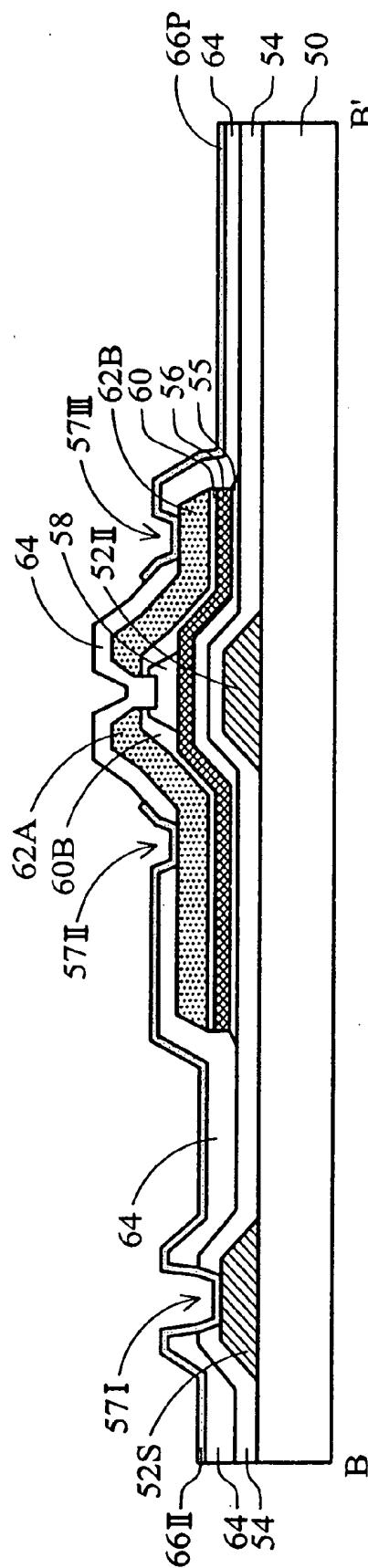


FIG. 4E

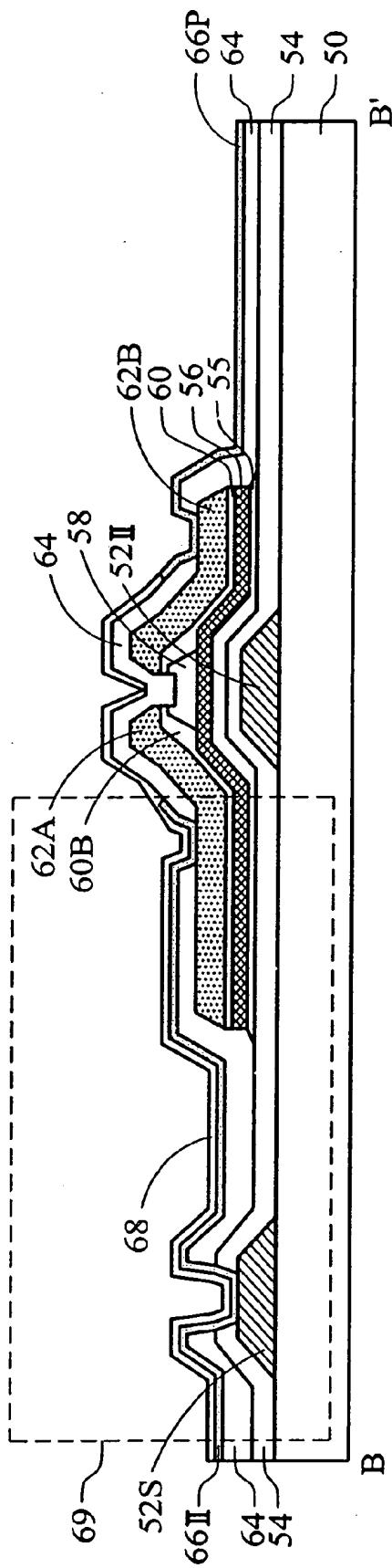


FIG. 4F

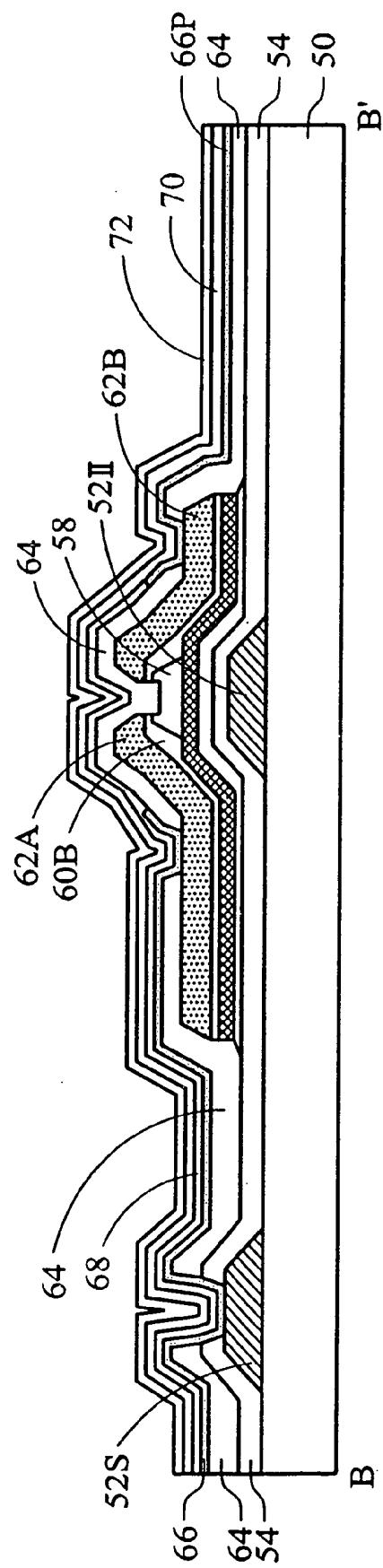
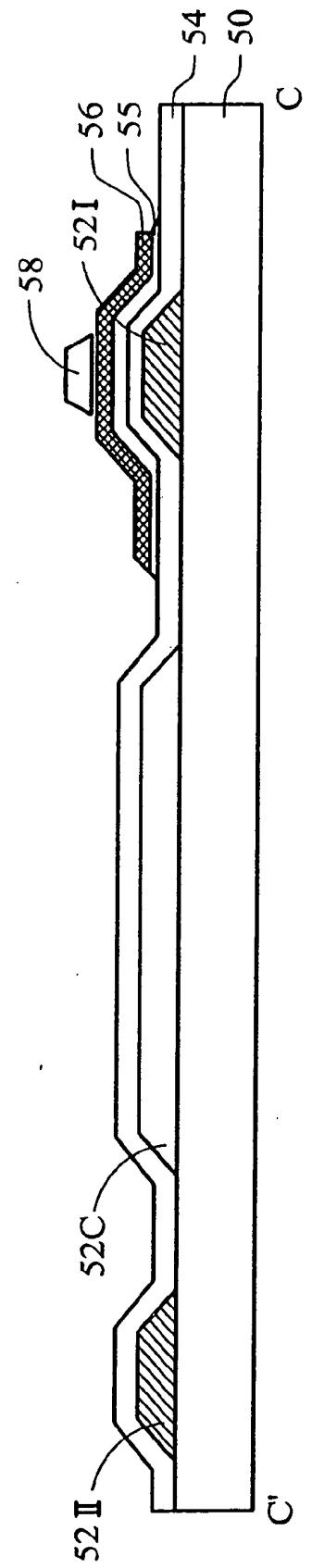
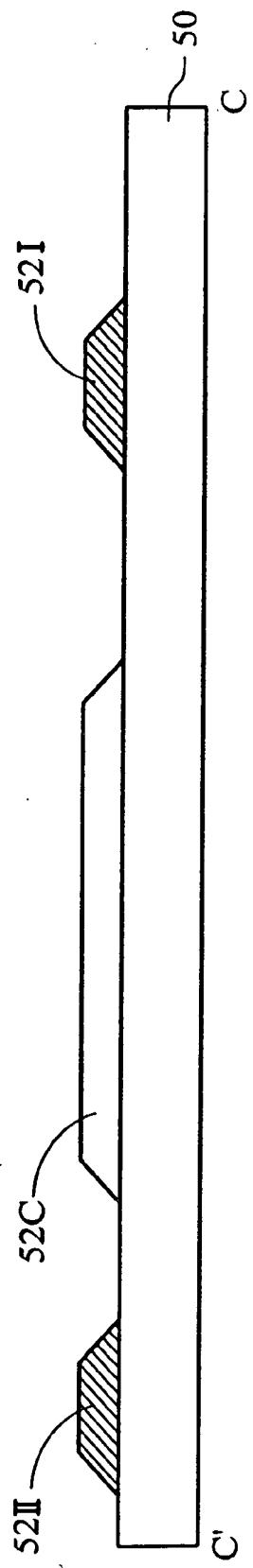


FIG. 4G



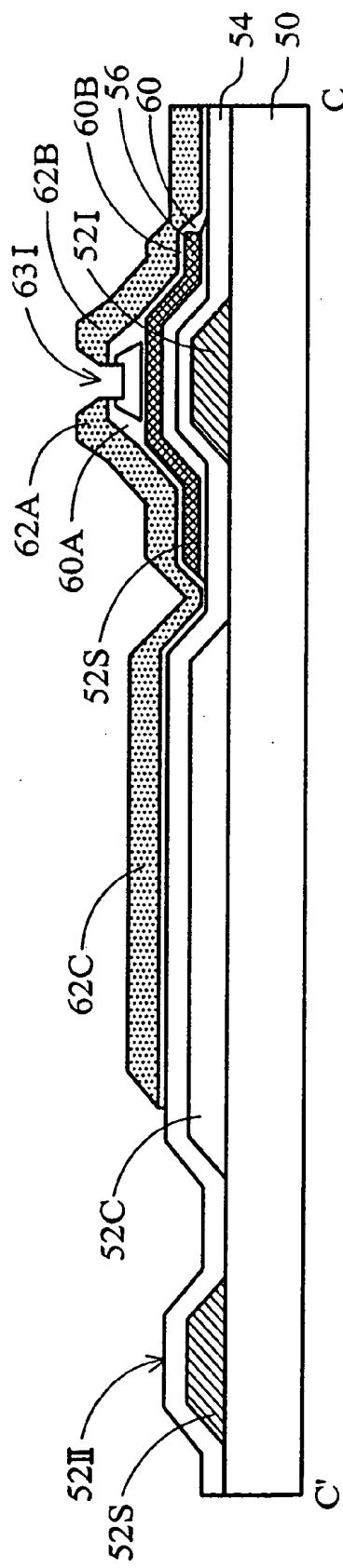


FIG. 5C

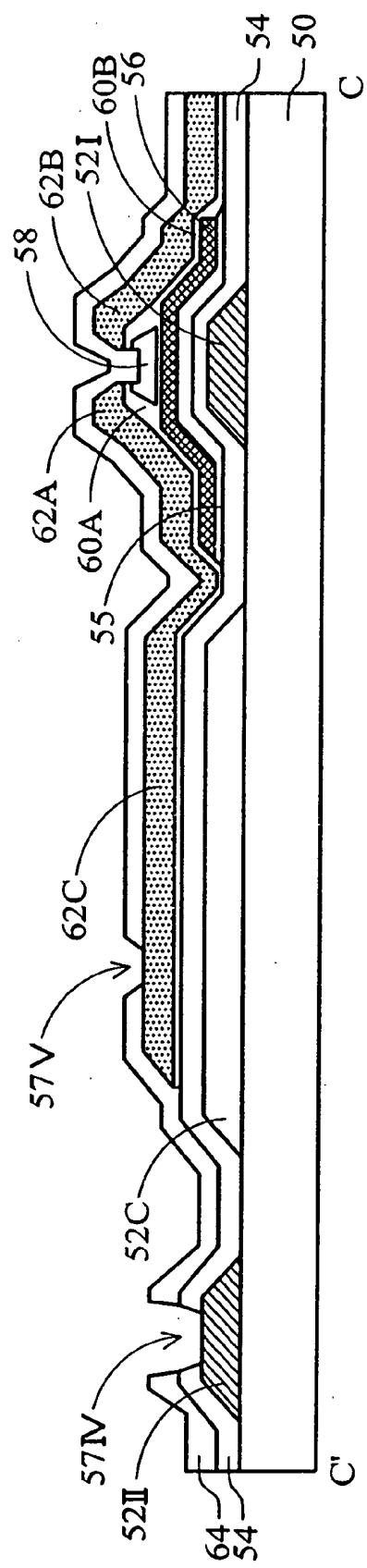


FIG. 5D

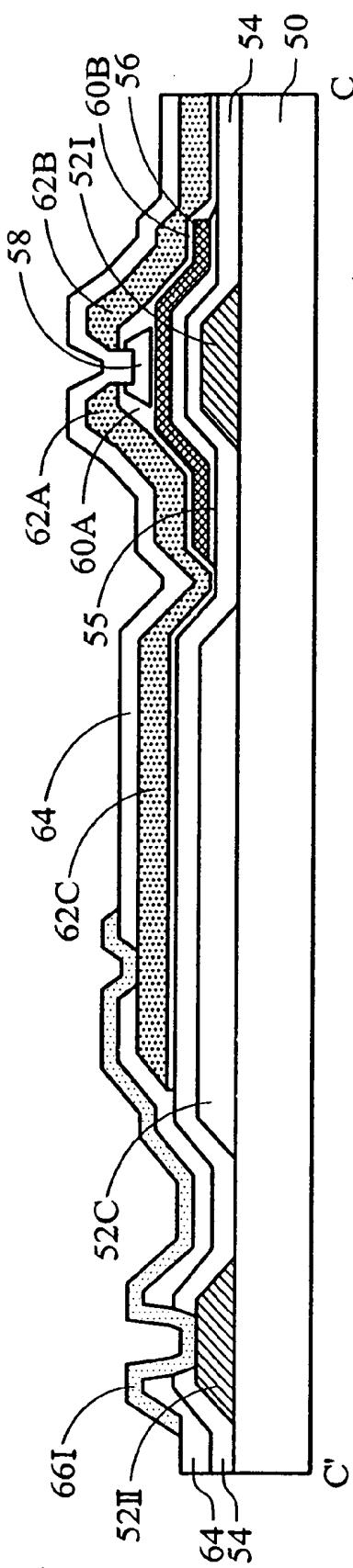


FIG. 5E

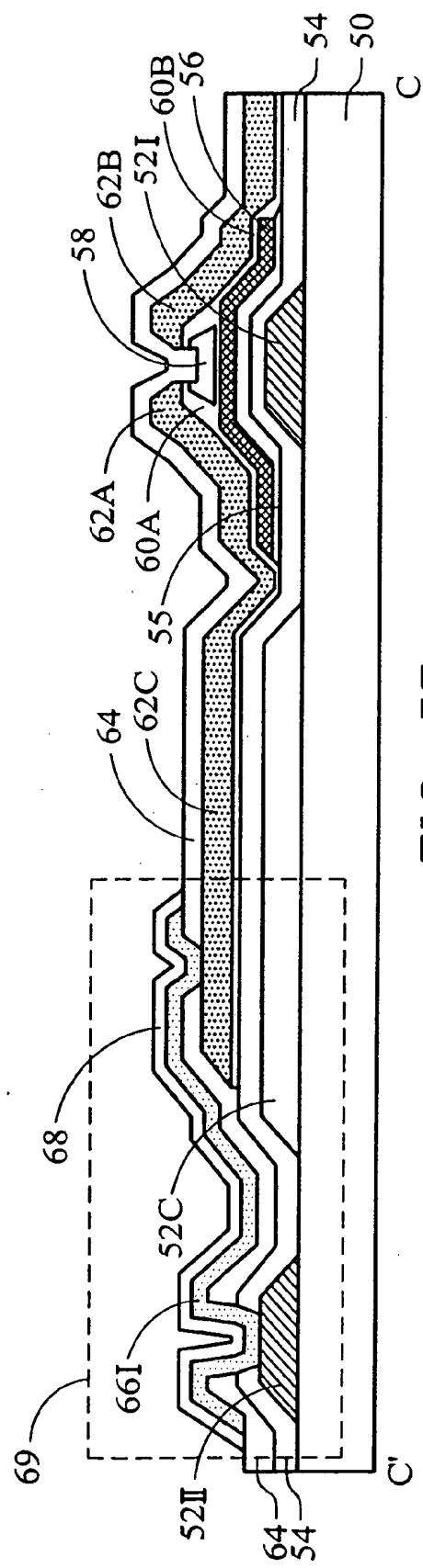


FIG. 5F

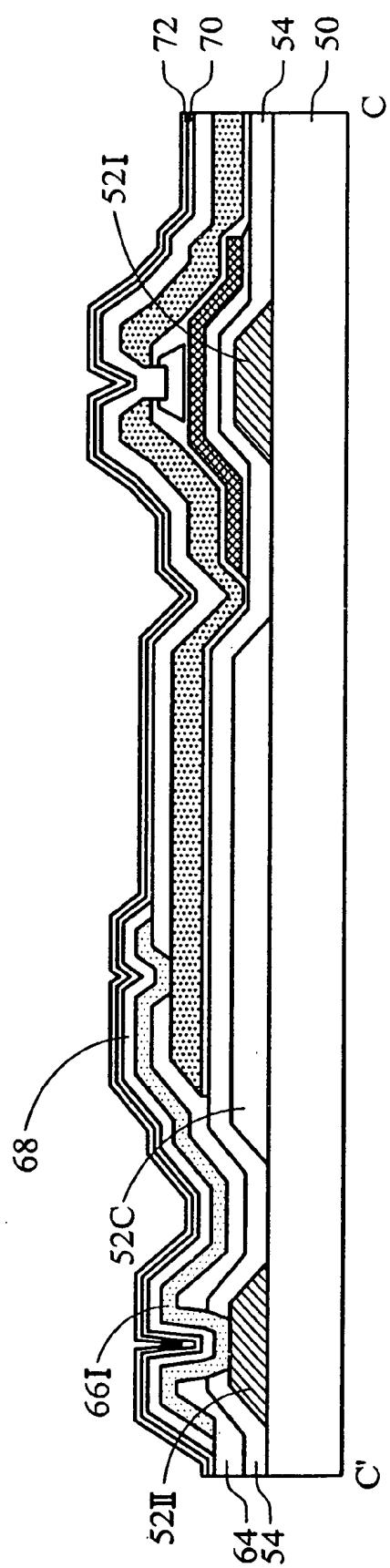


FIG. 5G

ACTIVE MATRIX ORGANIC LIGHT EMITTING DISPLAY AND METHOD OF FORMING THE SAME

BACKGROUND OF THE INVENTION

[0001] 1. Field of the Invention

[0002] The present invention relates to an active matrix organic light emitting display (AM-OLED) with an amorphous silicon thin film transistor (a-Si:H TFT) as a driving device and, more particularly, to an AM-OLED with a light-shielding structure that isolates parasitic OLEDs outside a display area and prevents damage to an amorphous silicon layer from subsequent surface treatments.

[0003] 2. Description of the Related Art

[0004] In accordance with driving methods, an organic light emitting display (OLED) can be an active matrix type or a positive matrix type. The active matrix organic light emitting display (AM-OLED) is driven by electric currents, in which each of the matrix-array pixel areas has at least one thin film transistor (TFT), serving as a switch, to modulate the driving current based on the variation of capacitor storage potential so as to control the brightness and gray level of the pixel areas. At present, the AM-OLED is driven by two TFTs in each pixel area, and, alternatively, the AM-OLED is driven by four TFTs in each pixel area.

[0005] Concerned with the luminescent principle of the AM-OLED, an electric current is applied to a specific organic lamination to change electricity into luminescence. The AM-OLED has panel luminescence with thin-type and light-weight characteristics, spontaneous luminescence with high luminescent efficiency and low driving voltage, and advantages of view angle, high contrast, high-response speed, full color and flexibility. As for the fabrication of the TFTs in the AM-OLED, an amorphous silicon (a-Si:H) TFT process that has been popularly applied to the fabrication of large-size liquid crystal displays (LCDs) is integrated into the AM-OLED process.

[0006] Use of two a-Si:H TFTs in each pixel area is an example to describe the conventional a-Si:H TFT process. FIG. 1 is a top view showing an a-Si:H TFT of an AM-OLED according to prior art. The AM-OLED comprises a plurality of pixel areas 10 arranged in a matrix form that are constituted by a plurality of data lines 12 extending along a Y direction and a plurality of source lines (also called V_{dd} lines) 14 extending along an X direction. Also, each pixel area 10 comprises two scanning lines 16 extending along the X direction, two a-Si:H TFTs 18 respectively disposed over the two scanning lines 16, a pixel electrode 20 of rectangular-shaped transparent conductive material disposed between the two scanning lines 16, and a capacitor 22.

[0007] In general, the a-Si:H TFT process can be an etching stopper type and a back channel type. Hereinafter, use of the etching stopper type is an example to describe the a-Si:H TFT process of the prior art. FIG. 2A is a sectional diagram along line A-A' of FIG. 1 to show the a-Si:H TFT 18. First, a first metal layer is deposited on a transparent substrate 30 and then patterned as the source line 14, the scanning line 16 and a bottom electrode of the capacitor 22. Next, a first insulating layer 32, a second insulating layer 34 and an a-Si:H layer 36 are successively deposited on the entire surface of the transparent substrate 30. Then, using

photolithography and etching to remove parts of the second insulating layer 34 and the a-Si:H layer 36, an island structure is patterned over the predetermined area of the a-Si:H TFT 18. Also, the second insulating layer 34 and the a-Si:H layer 36 disposed over the source line 14 are completely removed. Thereafter, an etch stopper 38 is formed on the island structure over the predetermined area of a gate electrode. After a doped amorphous silicon layer 40 and a second metal layer 42 are successively deposited on the entire surface of the transparent substrate 30, photolithography and etching are used to remove parts of the doped amorphous silicon layer 40 and the second metal layer 42, thus the second metal layer 42 is patterned as the data line 12 and an upper electrode of the capacitor 22. It is noted that the doped amorphous silicon layer 40 and the second metal layer 42 disposed on the island structure remain, and the doped amorphous silicon layer 40 and the second metal layer 42 disposed on the source line 14 are completely removed. Next, using photolithography and etching to form an opening on the island structure over the predetermined area of a gate electrode, the second metal layer 42 is separated as source/drain electrodes 42A and 42B and the doped amorphous silicon layer 40 is separated as source/drain diffusion regions 40A and 40B. Thus, the amorphous silicon layer 36 serves as a channel region.

[0008] Next, a protection layer 44 is deposited on the entire surface of the transparent substrate 30 and then patterned to form at least a first via 45I, a second via 45II and a third via 45III. The first via 45I and the second via 45II respectively expose parts of the source/drain electrodes 42A and 42B. The third via 45III passes through the first insulating layer 32 to expose a part of the source line 14. Finally, a transparent-conductive ITO layer 46 is deposited and patterned on the entire surface of the transparent substrate 30 to serve as the rectangular-shaped pixel electrode 20. Also, the ITO layer 46 covers the exposed areas of the first via 45I, the second via 45II and the third via 45III to provide electrical connections.

[0009] FIG. 2B is a sectional diagram along line A-A' of FIG. 1 to show a parasitic OLED according to the prior art. When the above-described a-Si:H TFT process is completed, a surface treatment is required before the vapor deposition of a organic/polymer luminescent layer 47 and a cathode metal layer 48. However, the surface treatment normally employs a rinsing process with UV/O₃ light or O₂ plasma that damages the amorphous silicon layer 36, causing an increased threshold voltage or leakage current. To solve this problem, for the ordinary TFT-LCD process, an annealing treatment additionally applied to the amorphous silicon layer 36 can restore the damaged surface. Nevertheless, for the a-Si:H TFT process, because of the limitation of the subsequent vapor deposition of a organic/polymer luminescent layer 47, it is impossible to use the annealing treatment to restore the damaged surface.

[0010] In addition, with regard to the conventional five-mask a-Si:H TFT process, the ITO layer 46 not only serves as the pixel electrode 20, but also serves as an electrical bridge between the second metal layer and the second metal layer or between the second metal layer and the first metal layer. Thus, the ITO layer 46 outside the pixel electrode 20 forms a parasitic OLED area 49 that provides luminescence causing unnecessary power consumption and visual interference.

SUMMARY OF THE INVENTION

[0011] The present invention provides an AM-OLED with an a-Si:H TFT as a driving device and, more particularly, in which a light-shielding structure electrically isolates parasitic OLEDs outside a display area and prevents damage to an amorphous silicon layer from subsequent surface treatments.

[0012] The active matrix organic light emitting display (AM-OLED) has a plurality of pixel areas arranged in a matrix form. Each pixel area has at least two amorphous silicon TFTs, a display area and a light-shielding layer. The amorphous silicon TFT has an amorphous silicon layer serving as a channel region. The display area is formed by a transparent-conductive layer. The light-shielding layer covers at least the amorphous silicon layer of the amorphous silicon TFT and exposes the display area.

[0013] For a method of forming the AM-OLED, a first metal layer is formed on a transparent substrate and then patterned as a first scanning line extending along a X direction, a second scanning line extending along the X direction and an bottom electrode of a capacitor, wherein the bottom electrode of the capacitor is between the two scanning lines. Next, a first insulating layer is formed on the entire surface of the transparent substrate. Next, an island structure is formed on a predetermined TFT area over the first scanning line, wherein the island structure comprises a second insulating layer deposited on the first insulating layer and an amorphous silicon layer deposited on the second insulating layer. Then, an etching stopper is formed on the top of the island structure to cover a predetermined gate electrode of the predetermined TFT. Thereafter, a doped amorphous silicon layer and a second metal layer are formed on the island structure in sequence. Then, the second metal layer is patterned as a data line extending in a Y direction and an upper electrode of the capacitor, and an opening is formed on the island structure to separate the second metal layer as a source/drain electrode and separate the doped amorphous silicon layer as a source/drain diffusion region. Next, a protection layer is formed on the entire surface of the transparent substrate, and a first via and a second via are formed to expose one end of the second scanning line and one end of the upper electrode of the capacitor. Thereafter, a transparent-conductive layer is formed on the entire surface of the transparent substrate, and then patterned as a display area and two electrical-connecting areas that cover the exposed areas of the first via and the second via. Finally, a light-shielding layer is formed on the entire surface of the transparent substrate, wherein the light-shielding layer covers at least the amorphous silicon layer of the predetermined TFT and exposes the display area.

[0014] Accordingly, it is a principal object of the invention to provide the light-shielding layer to prevent damage to the amorphous silicon layer 56 from the UV light or plasma in the sequential rinsing process.

[0015] It is another object of the invention to decrease the threshold voltage and the leakage current caused by the damage to the amorphous silicon layer.

[0016] Yet another object of the invention is to provide a light-shielding layer to isolate the parasitic OLED area.

[0017] It is a further object of the invention to prevent unnecessary power consumption and visual interference caused by the luminescence of the parasitic OLED.

[0018] These and other objects of the present invention will become readily apparent upon further review of the following specification and drawings.

BRIEF DESCRIPTION OF THE DRAWINGS

[0019] FIG. 1 is a top view showing an a-Si:H TFT of an AM-OLED according to prior art.

[0020] FIG. 2A is a sectional diagram along line A-A' of FIG. 1 to show the a-Si:H TFT.

[0021] FIG. 2B is a sectional diagram along line A-A' of FIG. 1 to show a parasitic OLED according to the prior art.

[0022] FIGS. 3A to 3F are top views showing the a-Si:H TFT process according to the present invention.

[0023] FIGS. 4A to 4G are sectional diagrams along line B-B' of FIG. 3 to show the a-Si:H TFT process according to the present invention.

[0024] FIGS. 5A to 5G are sectional diagrams along line C-C' of FIG. 3 to show the a-Si:H TFT process according to the present invention.

[0025] Similar reference characters denote corresponding features consistently throughout the attached drawings.

DETAILED DESCRIPTION OF THE INVENTION

[0026] The present invention provide an AM-OLED with an a-Si:H TFT as a driving device and, more particularly, in which a light-shielding structure electrically isolates parasitic OLEDs outside a display area and prevents damage to an amorphous silicon layer from subsequent surface treatments.

[0027] Use of two a-Si:H TFTs in each pixel area is an example to describe the a-Si:H TFT process of the present invention. The AM-OLED comprises a plurality of pixel areas arranged in a matrix form that are constituted by a plurality of data lines extending along a Y direction and a plurality of source lines (also called V_{dd} lines) extending along an X direction. Also, each pixel area comprises two scanning lines extending along the X direction, two a-Si:H TFTs respectively disposed over the two scanning lines, a pixel electrode of rectangular-shaped transparent conductive material disposed between the two scanning lines, and a capacitor.

[0028] In general, the a-Si:H TFT process can be an etching stopper type or a back channel type. Hereinafter, use of the etching stopper type is an example to describe the a-Si:H TFT process of the present invention.

[0029] FIGS. 3A to 3F are top views showing the a-Si:H TFT process according to the present invention. FIGS. 4A to 4G are sectional diagrams along line B-B' of FIG. 3 to show the a-Si:H TFT process according to the present invention. FIGS. 5A to 5G are sectional diagrams along line C-C' of FIG. 3 to show the a-Si:H TFT process according to the present invention.

[0030] As shown in FIGS. 3A, 4A and 5A, a first metal layer 52 is deposited on a transparent substrate 50 and then patterned as a source line 52S extending along the X direction, a first scanning line 52I extending along the X direction, a second scanning line 52II extending along the X

direction, and a bottom electrode **52C** of a capacitor. Next, as shown in FIGS. 3B, 4B and 5B, a first insulating layer **54**, a second insulating layer **55** and an amorphous silicon layer **56** are successively deposited on the entire surface of the transparent substrate **50**. Preferably, the first insulating layer **54** is SiO_2 , SiN or SiON , and the second insulating layer **55** is SiO_2 , SiN or SiON . Then, using photolithography and etching to remove parts of the second insulating layer **55** and the amorphous silicon layer **56**, two island structures are respectively formed on the predetermined areas of the two a-Si:H TFTs over the two scanning lines **52I** and **52II**. Also, over the source line **52S**, the second insulating layer **55** and the amorphous silicon layer **56** are completely removed and a first via **57I** is formed in the first insulating layer **54** to expose a part of the source line **52S**. Thereafter, an etching stopper **58** is formed on the predetermined area of the gate electrode within the island structure.

[0031] As shown in FIGS. 3C, 4C and 5C, a doped amorphous silicon layer **60** and a second metal layer **62** are successively deposited on the entire surface of the transparent substrate **50**, in which an n^+ -doped polysilicon material is preferred to form the doped amorphous silicon layer **60**. Then, using photolithography and etching to remove parts of the doped amorphous silicon layer **60** and the second metal layer **62**, the second metal layer **62** is patterned as a data line **62D** extending along the Y direction and an upper electrode **62C** of the capacitor. It is noted that the doped amorphous silicon layer **60** and the second metal layer **62** remain on the island structure, and completely removed from the source line **52S**. Next, using photolithography and etching to form two openings **63I** and **63II** respectively on the predetermined area of the gate electrodes in the two island structures, the second metal layer **62** is separated as a source/drain electrode **62A/62B**, the doped amorphous silicon layer **60** is separated as a source/drain diffusion region **60A/60B**, and the amorphous silicon layer **56** serves as a channel region. This completes the first a-Si:H TFT (TFT1) and the second a-Si:H TFT (TFT2).

[0032] As shown in FIGS. 3D, 4D and 5D, a protection layer **64** is deposited on the entire surface of the transparent substrate **50**, and then at least a second via **57II**, a third via **57III**, a fourth via **57IV** and a fifth via **57V** are formed in the protection layer **64** by photolithography and etching. Meanwhile, the first via **57I** is exposed. The second via **57II** and the third via **57III** expose the second metal layer **62** in the vicinity of the source/drain electrodes **62A/62B** of the second a-Si:H TFT (TFT2). The fourth via **57IV** exposes one end of the second scanning line **52I**, and the fifth via **57V** exposes a part of the upper electrode **62C** of the capacitor.

[0033] As shown in FIGS. 3E, 4E and 5E, a first transparent-conductive layer **66** of ITO is deposited on the entire surface of the transparent substrate **50**, and then patterned as a rectangular display area **66P**, and two electrical-connecting bridges **66I** and **66II** that cover the exposed areas of the vias **57I**, **57II**, **57III**, **57IV** and **57V**. The first electrical-connecting bridge **66I** electrically connects the upper electrode **62C** of the capacitor and the second scanning line **52II**, and the second electrical-connecting bridge **66II** electrically connects the SOURCE LINE **52S** and the second scanning line **52II**.

[0034] As shown in FIGS. 3F, 4F and 5F, a light-shielding layer **68** is formed on the transparent substrate **50** to cover,

at least, the two electrical-connecting bridges **66I** and **66II** and expose the display area **66P**. Thus, the light-shielding layer **68** shields the amorphous silicon layer **56** and isolates a parasitic OLED area **69**. To simplify the process, the light-shielding layer **68** is patterned to cover any area outside the display area **66**. Preferably, the light-shielding layer **68** is an opaque and insulating single-layered material (such as CrO_x), a polymer/resin-containing and double-layered material (such as polyimide/carbon), or an opaque and metallic double-layered material (such as SiO_x/Cr).

[0035] Finally, as shown in FIGS. 4G and 5G, the surface is processed by a rinsing process with UV/O_3 or O_2 plasma, and then an organic/polymer luminescent layer **70** and a cathode metal layer **72** are successively deposited on the entire surface by a vapor deposition. This completes the AM-OLED process.

[0036] Compared with the prior art, the present invention provides the light-shielding layer **68** outside the display area **66P**, preventing damage to the amorphous silicon layer **56** from UV light or plasma in the sequential rinsing process, decreasing the threshold voltage and the leakage current caused by the damage to the amorphous silicon layer **56**. Also, because the light-shielding layer **68** covers the electrical-connecting bridges **66I** and **66II** to isolate the parasitic OLED area **69**, unnecessary power consumption and visual interference caused by the luminescence of the parasitic OLED are prevented.

[0037] It is to be understood that the present invention is not limited to the embodiments described above, but encompasses any and all embodiments within the scope of the following claims.

1. An active matrix organic light emitting display (AM-OLED) comprising a plurality of pixel areas arranged in a matrix form, each pixel area comprising:

at least two amorphous silicon TFTs, in which the amorphous silicon TFT comprises an amorphous silicon layer serving as a channel region;

a display area formed by a transparent-conductive layer; and

a light-shielding layer which covers at least the amorphous silicon layer of the amorphous silicon TFT and exposes the display area.

2. The active matrix organic light emitting display (AM-OLED) according to claim 1, wherein the light-shielding layer is of an opaque and insulating material.

3. The active matrix organic light emitting display (AM-OLED) according to claim 1, wherein the light-shielding layer is a CrO_x single-layered material, a polyimide/carbon double-layered material, or a SiO_x/Cr double-layered material.

4. The active matrix organic light emitting display (AM-OLED) according to claim 1, wherein the light-shielding layer covers any area outside the display area.

5. The active matrix organic light emitting display (AM-OLED) according to claim 1, wherein the light-shielding layer covers the transparent-conductive layer outside the display area.

6. The active matrix organic light emitting display (AM-OLED) according to claim 1, wherein the transparent-conductive layer is ITO (indium tin oxide) or IZO (indium zinc oxide).

7. The active matrix organic light emitting display (AM-OLED) according to claim 1, wherein each pixel area is defined by orthogonal intersections between two adjacent data lines and two adjacent source lines, and each pixel area comprises at least one capacitor.

8. The active matrix organic light emitting display (AM-OLED) according to claim 1, wherein the surface of each pixel area is covered with an organic luminescent layer and a cathode metal layer.

9-19. (canceled)

* * * * *

专利名称(译)	有源矩阵有机发光显示器及其形成方法		
公开(公告)号	US20040232420A1	公开(公告)日	2004-11-25
申请号	US10/869250	申请日	2004-06-15
[标]申请(专利权)人(译)	友达光电股份有限公司		
申请(专利权)人(译)	友达光电.		
当前申请(专利权)人(译)	友达光电.		
[标]发明人	LEE HSIN HUNG SUNG CHIH FENG		
发明人	LEE, HSIN-HUNG SUNG, CHIH-FENG		
IPC分类号	H01L27/32 H01L51/52 H01L29/04 H01L31/036 G02F1/1343		
CPC分类号	H01L27/3272 H01L51/5281 H01L51/5284		
优先权	091109072 2002-05-01 TW		
其他公开文献	US7176070		
外部链接	Espacenet USPTO		

摘要(译)

有源矩阵有机发光显示器 (AM-OLED) 及其形成方法。AM-OLED具有以矩阵形式布置的多个像素区域。每个像素区域具有至少两个非晶硅 TFT，显示区域和遮光层。非晶硅TFT具有用作沟道区的非晶硅层。显示区域由透明导电层形成。遮光层至少覆盖非晶硅TFT的非晶硅层并暴露显示区域。

